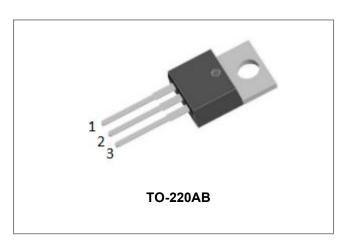






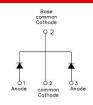
### MBR30150CTL SCHOTTKY RECTIFIER



#### **Features**

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced
- mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: Tin Lead-free plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Circuit Diagram**



#### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

#### Maximum Ratings(limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	150	٧
Average Rectified Forward Current	I <sub>F (AV)</sub>	Tc=120°C, in DC	15(Per Leg) 30(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	408	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@ 15A, Pulse, T <sub>J</sub> = 25 °C	0.79	0.90	V
	$V_{F2}$	@ 15A, Pulse, T <sub>J</sub> = 125 °C	0.66	0.78	V
Reverse Current(Per Leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	0.001	1.0	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_R, T_J = 125  ^{\circ}\text{C}$	1	15	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25 ^{\circ}C$ $f_{SIG} = 1MHz$	480	500	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •



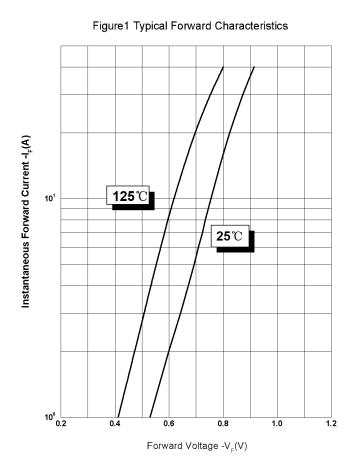


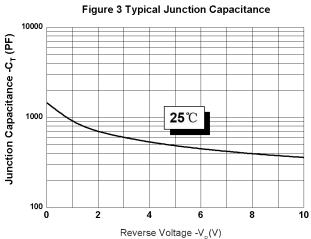


# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>0</sub> JC	DC operation	2.2	°C/W
Approximate Weight	wt	-	2	g

### **Ratings and Characteristics Curves**





<sup>•</sup> China - Germany - Korea - Singapore - United States •

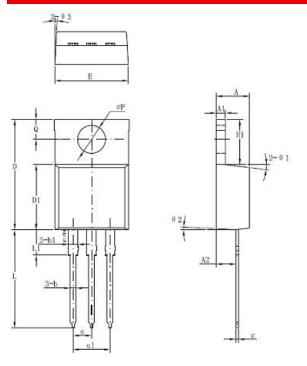
<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •





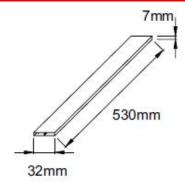


#### **Mechanical Dimensions TO-220AB**

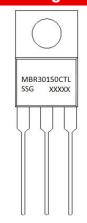


Symbol	Dimensions in millimeters		
	Min	Max	
Α	3.56	-	4.83
A1	0.51	-	1.4
A2	2.03	-	2.92
b	0.38	-	1.02
b1	1.14	-	1.78
С	0.31	-	0.61
D	14.22	-	16.51
D1	8.38	-	9.42
E	9.65	-	10.67
е	-	2.54	-
e1	-	5.08	-
H1	5.84	-	6.86
L	12.7	-	14.73
L1	-	-	6.35
ФР	-	3.56	-
Q	2.54	-	3.43

### **Tube Specification**



### **Marking Diagram**



Where XXXXX is YYWWL

 MBR
 = Device Type

 30
 = Forward Current (30A)

 150
 = Reverse Voltage(150V)

 CTL
 = Configuration

 SSG
 = SSG

SSG = SSG
YY = Year
WW = Week
L = Lot Number

**Cautions:** Molding resin Epoxy resin UL:94V-0

## **Ordering Information**

Device	Package	Shipping	
MBR30150CTL	TO-220AB (Pb-Free)	50 pcs/ tube	

- China Germany Korea Singapore United States •
- http://www.smc-diodes.com sales@ smc-diodes.com •







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